

Complementary Silicon Plastic Power Transistors

TIP41G, TIP41AG, TIP41BG, TIP41CG (NPN), TIP42G, TIP42AG, TIP42BG, TIP42CG (PNP)

Designed for use in general purpose amplifier and switching applications.

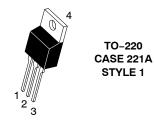
Features

- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

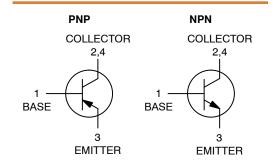
MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _{CEO}	Collector–Emitter Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	40 60 80 100	Vdc
V _{CB}	Collector-Base Voltage TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	40 60 80 100	Vdc
V _{EB}	Emitter-Base Voltage	5.0	Vdc
I _C	Collector Current - Continuous	6.0	Adc
I _{CM}	Collector Current - Peak	10	Adc
I _B	Base Current	2.0	Adc
P _D	Total Power Dissipation @ T _C = 25°C Derate above 25°C	65 0.52	W W/°C
P _D	Total Power Dissipation @ T _A = 25°C Derate above 25°C	2.0 0.016	W W/°C
E	Unclamped Inductive Load Energy (Note 1)	62.5	mJ
T _J , T _{stg}	Operating and Storage Junction, Temperature Range	-65 to +150	°C
HBM	ESD - Human Body Model	3B	V
MM	ESD - Machine Model	С	V

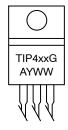
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS



MARKING DIAGRAM



TIP4xx = Device Code xx = 1, 1A, 1B, 1C 2, 2A, 2B, 2C A = Assembly Location Y = Year

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

^{1.} $I_C = 2.5 \text{ A}$, L = 20 mH, P.R.F. = 10 Hz, $V_{CC} = 10 \text{ V}$, $R_{BE} = 100 \Omega$.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, <u>SOLDERRM/D</u>.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	1.67	°C/W
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	57	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Min	Characteristic	Symbol	Max	Unit
FF CHARA	CTERISTICS			
40 60 80 100	Collector-Emitter Sustaining Voltage (Note 2) (I _C = 30 mAdc, I _B = 0) TIP41G, TIP42G TIP41AG, TIP42AG TIP41BG, TIP42BG TIP41CG, TIP42CG	V _{CEO(sus)}	- - - -	Vdc
-	Collector Cutoff Current $(V_{CE}=30\ Vdc,\ I_B=0)$ TIP41G, TIP41AG, TIP42G, TIP42AG $(V_{CE}=60\ Vdc,\ I_B=0)$ TIP41BG, TIP41CG, TIP42BG, TIP42CG	I _{CEO}	0.7 0.7	mAdc
- - -	Collector Cutoff Current $ (V_{CE} = 40 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41G}, \text{TIP42G} $ $ (V_{CE} = 60 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41AG}, \text{TIP42AG} $ $ (V_{CE} = 80 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41BG}, \text{TIP42BG} $ $ (V_{CE} = 100 \text{ Vdc}, V_{EB} = 0) $ $ \text{TIP41CG}, \text{TIP42CG} $	I _{CES}	400 400 400 400	μAdc
-	Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	1.0	mAdc
N CHARAC	CTERISTICS (Note 2)			
30 15	DC Current Gain ($I_C = 0.3$ Adc, $V_{CE} = 4.0$ Vdc) ($I_C = 3.0$ Adc, $V_{CE} = 4.0$ Vdc)	h _{FE}	- 75	-
-	Collector-Emitter Saturation Voltage (I _C = 6.0 Adc, I _B = 600 mAdc)	V _{CE(sat)}	1.5	Vdc
	Base–Emitter On Voltage (I _C = 6.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	2.0	Vdc
YNAMIC C	HARACTERISTICS			
3.0	Current-Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)	f _T	-	MHz
20	Small-Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

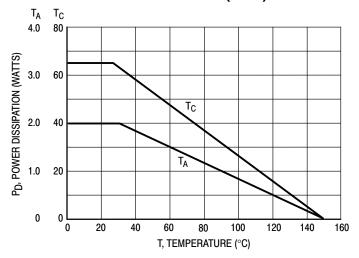
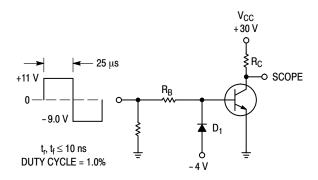


Figure 1. Power Derating



 R_{B} and R_{C} VARIED TO OBTAIN DESIRED CURRENT LEVELS

D $_1$ MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I $_B\approx 100$ mA MSD6100 USED BELOW I $_B\approx 100$ mA

Figure 2. Switching Time Test Circuit

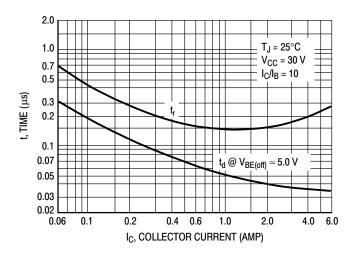


Figure 3. Turn-On Time

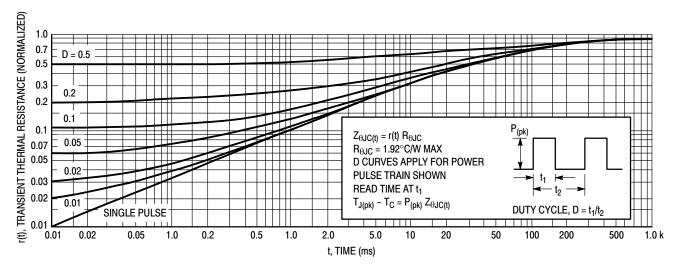


Figure 4. Thermal Response

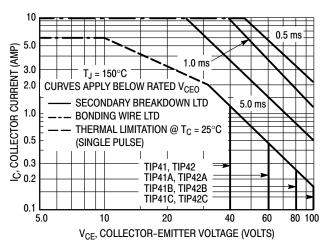


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

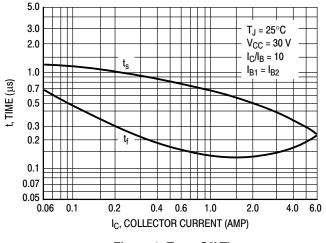


Figure 6. Turn-Off Time

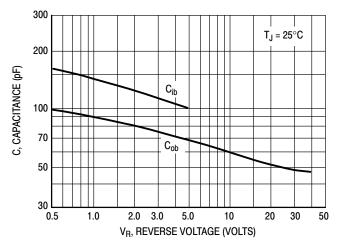


Figure 7. Capacitance

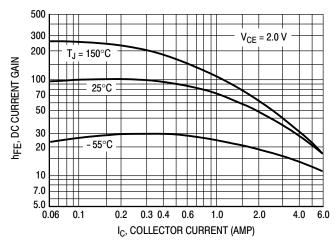


Figure 8. DC Current Gain

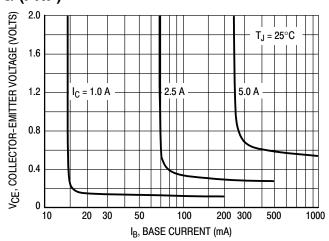


Figure 9. Collector Saturation Region

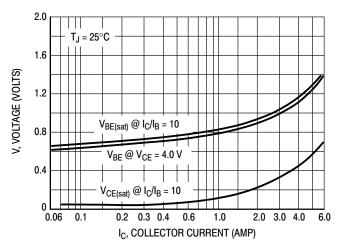


Figure 10. "On" Voltages

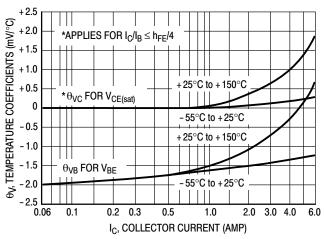


Figure 11. Temperature Coefficients

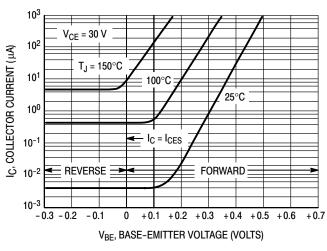


Figure 12. Collector Cut-Off Region

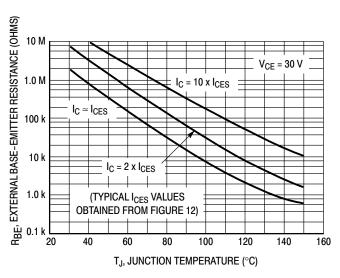


Figure 13. Effects of Base-Emitter Resistance

ORDERING INFORMATION

Device	Package	Shipping
TIP41BG	TO-220 (Pb-Free)	50 Units / Rail
TIP41CG	TO-220 (Pb-Free)	50 Units / Rail
TIP42AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42CG	TO-220 (Pb-Free)	50 Units / Rail

DISCONTINUED (Note 3)

TIP41G	TO-220 (Pb-Free)	50 Units / Rail
TIP41AG	TO-220 (Pb-Free)	50 Units / Rail
TIP42G	TO-220 (Pb-Free)	50 Units / Rail
TIP42BG	TO-220 (Pb-Free)	50 Units / Rail

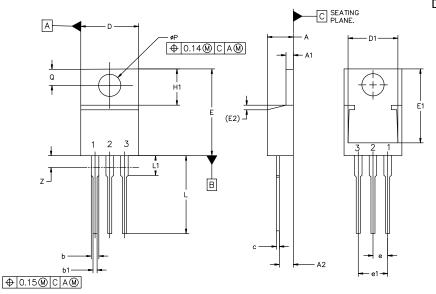
^{3.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.





TO-220-3 10.10x15.12x4.45, 2.54P CASE 221A **ISSUE AL**

DATE 05 FEB 2025



NOM 4.45 1.28 2.42	MAX 4.83 1.41 2.79		
1.28	1.41		
2.42			
	2.79		
4 7 4			
1.54	1.52		
0.80	0.96		
0.49	0.61		
10.10	10.53		
8.63	8.83		
15.12	15.75		
12.78	12.98		
1.27 REF			
	0.49 10.10 8.63 15.12 12.78		

MILLIMETERS						
DIM	MIN	NOM	MAX			
е	2.42	2.54	2.66			
e1	4.83	5.08	5.33			
H1	5.97	6.22	6.47			
L	12.70	13.49	14.27			
L1	2.80	3.45	4.10			
Q	2.54	2.79	3.04			
ØΡ	3.60	3.85	4.09			
Z			3.48			

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:	:	STYLE 12:	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

DOCUMENT NUMBER:	98ASB42148B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-220-3 10.10x15.12x4.45, 2.54P		PAGE 1 OF 1		

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales